

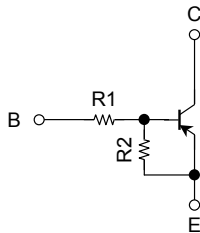
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process) (Bias Resistor Built-in Transistor)

RN2961FE, RN2962FE, RN2963FE RN2964FE, RN2965FE, RN2966FE

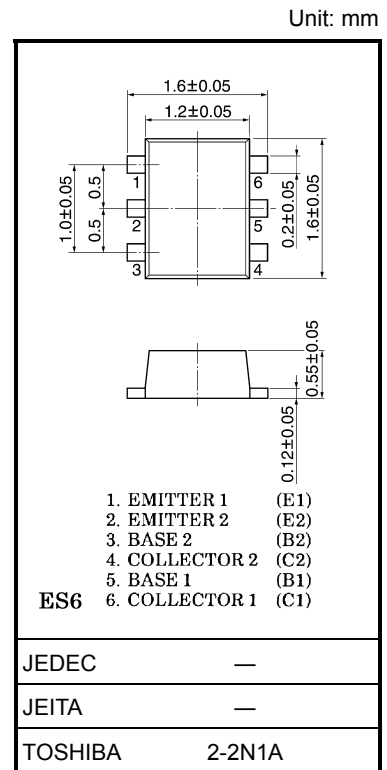
Switching, Inverter Circuit, Interface Circuit and
Driver Circuit Applications

- Two devices are incorporated into an Extreme-Super-Mini (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enables the manufacture of ever more compact equipment and lowers assembly cost.
- Complementary to RN1961FE~RN1966FE

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2961FE	4.7	4.7
RN2962FE	10	10
RN2963FE	22	22
RN2964FE	47	47
RN2965FE	2.2	47
RN2966FE	4.7	47



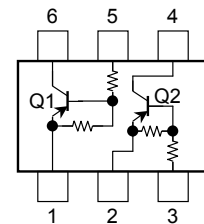
Weight: 0.003 g (typ.)

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Rating	Unit
Collector-base voltage	RN2961FE~2966FE	V_{CB0}	-50	V
Collector-emitter voltage		V_{CEO}	-50	V
Emitter-base voltage	RN2961FE~2964FE	V_{EBO}	-10	V
	RN2965FE, 2966FE		-5	
Collector current	RN2961FE~2966FE	I_C	-100	mA
Collector power dissipation		P_C (Note)	100	mW
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55~150	°C

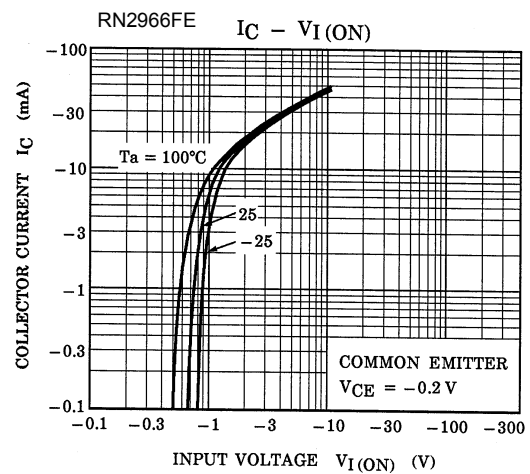
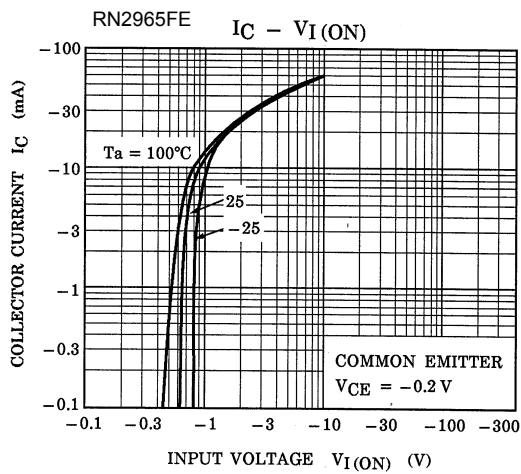
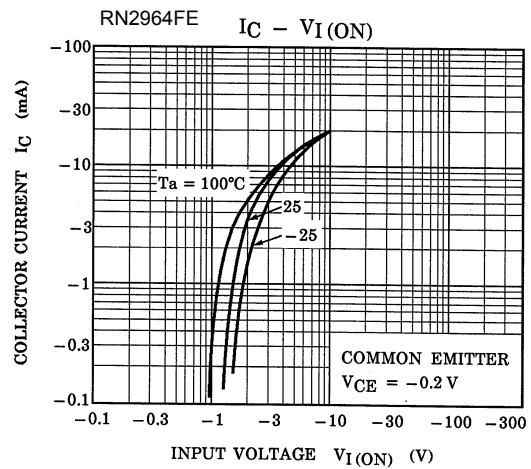
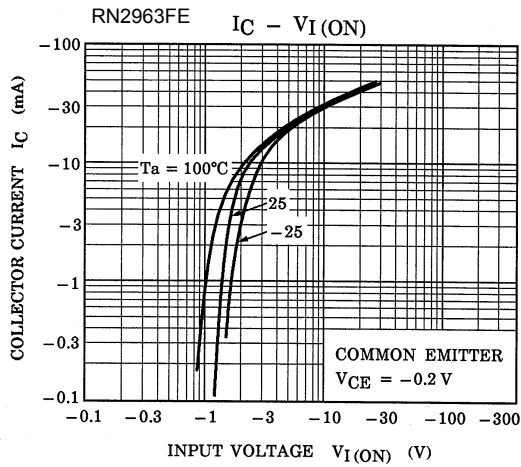
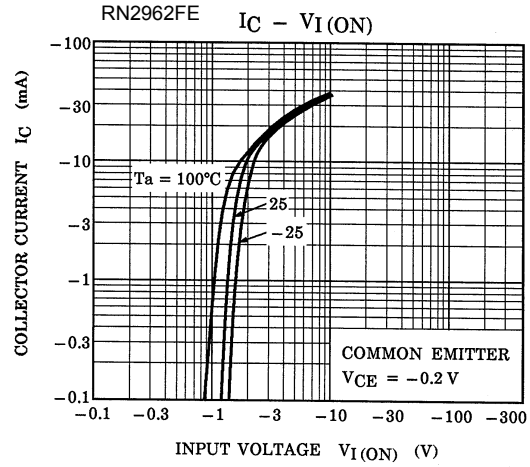
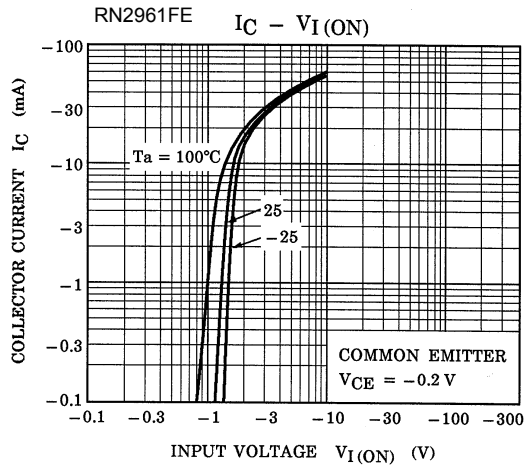
Note: Total rating

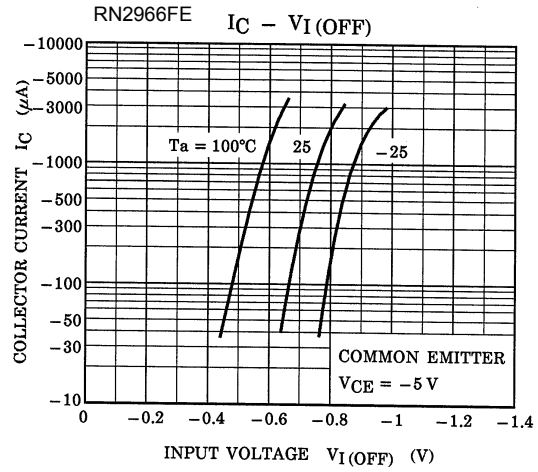
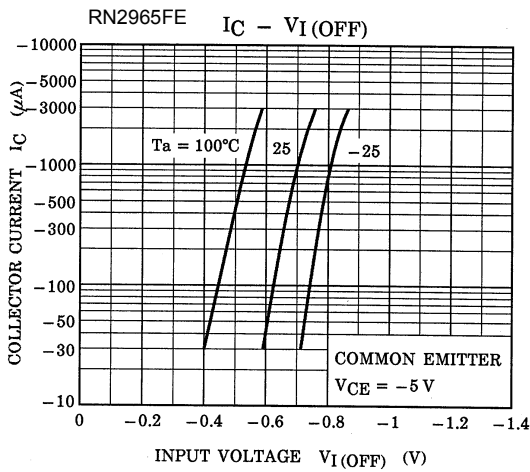
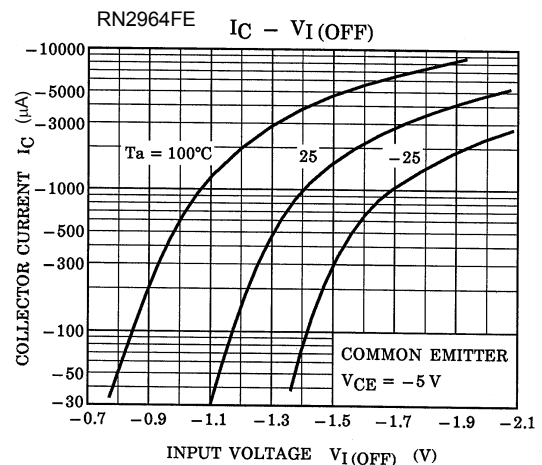
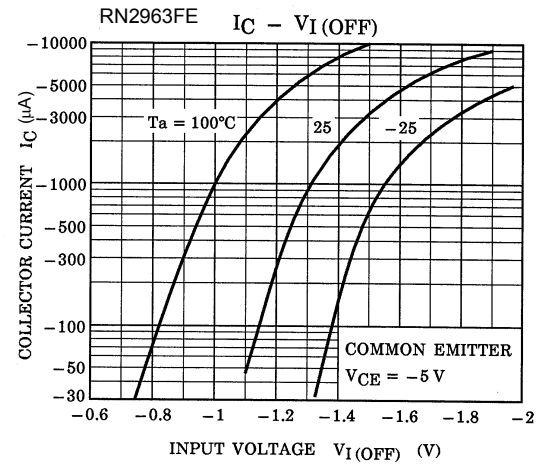
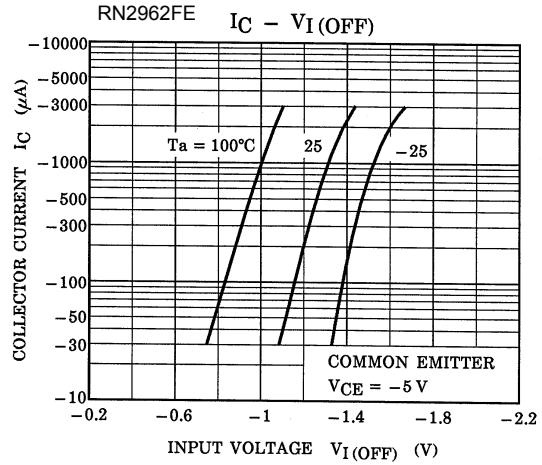
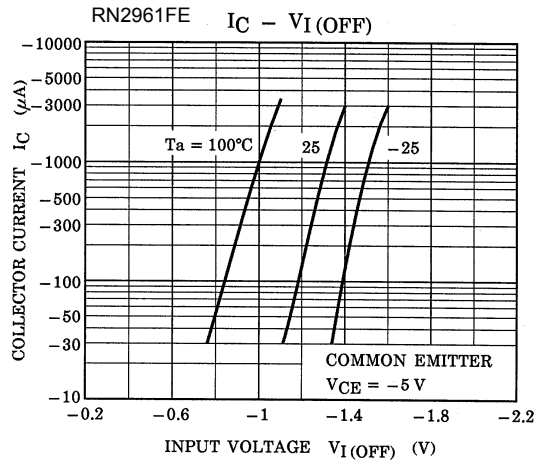
Equivalent Circuit (top view)

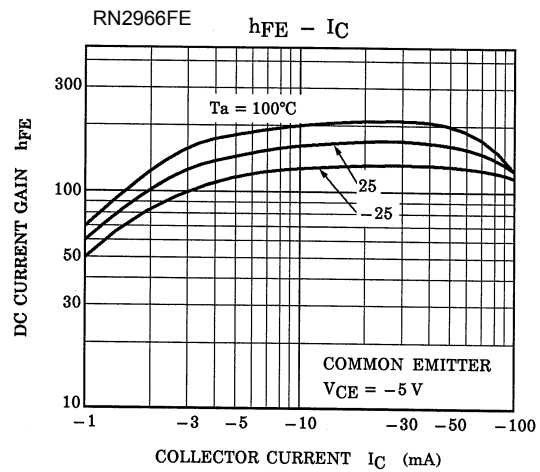
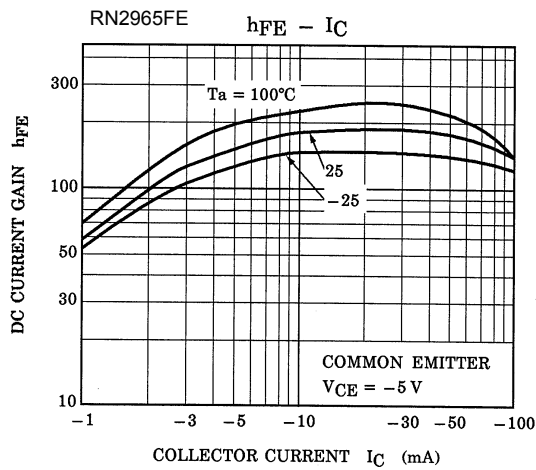
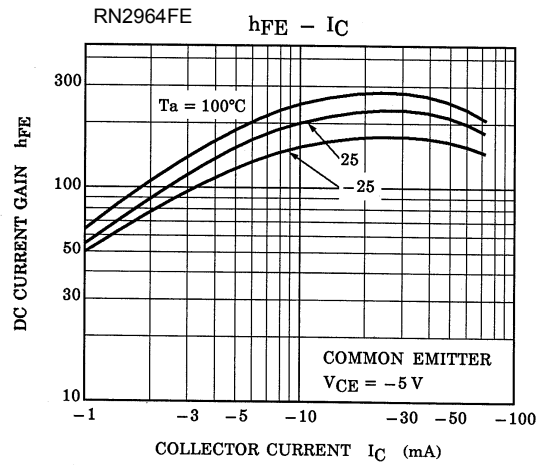
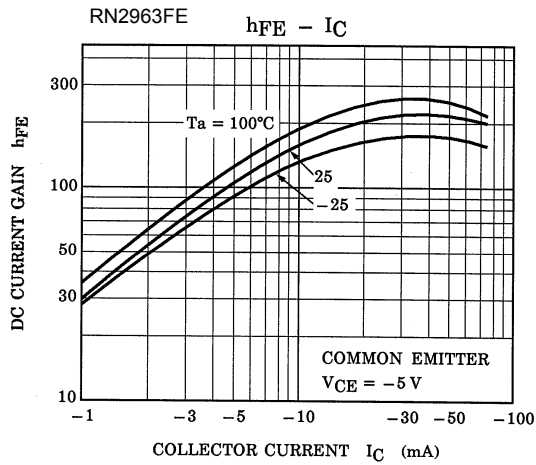
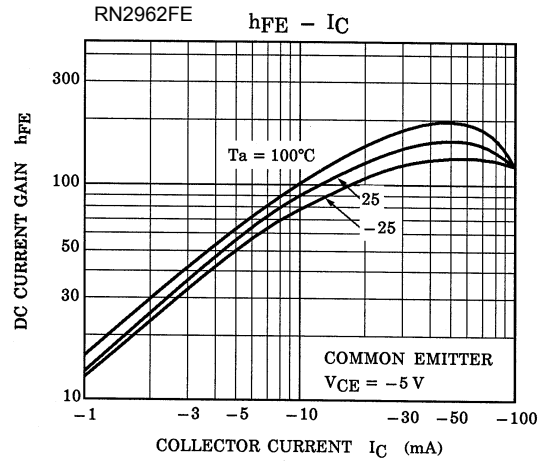
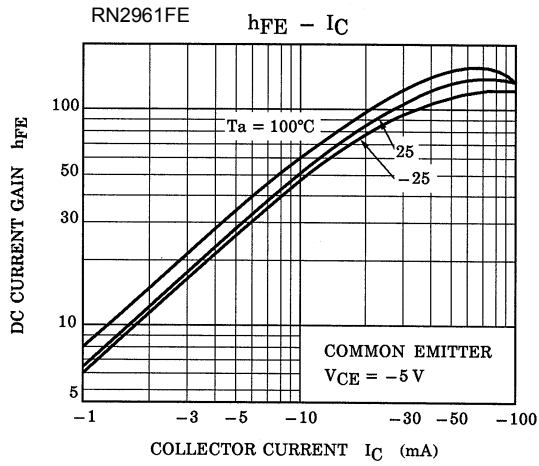


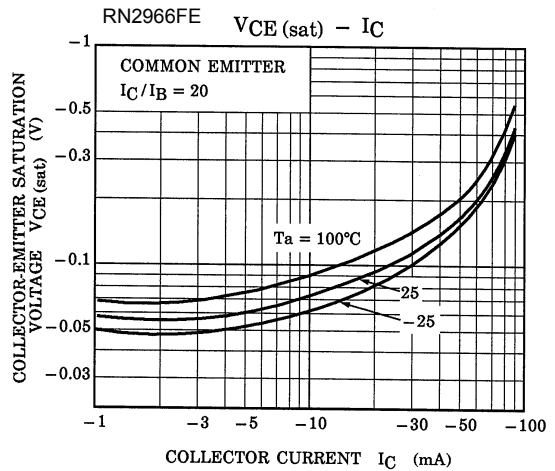
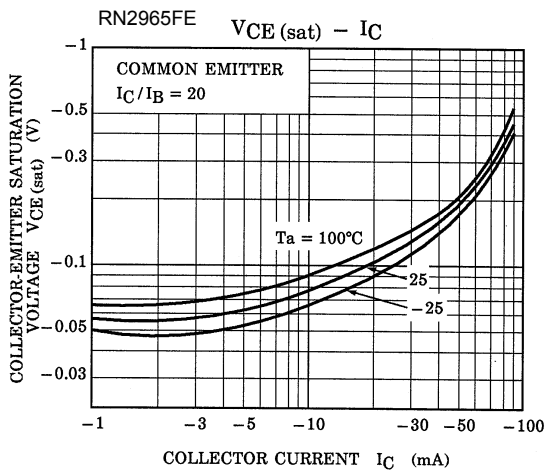
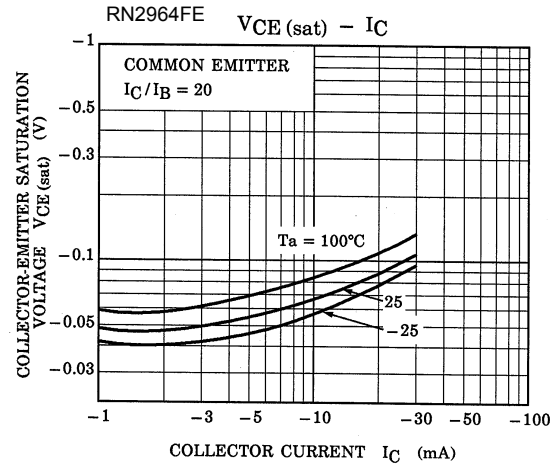
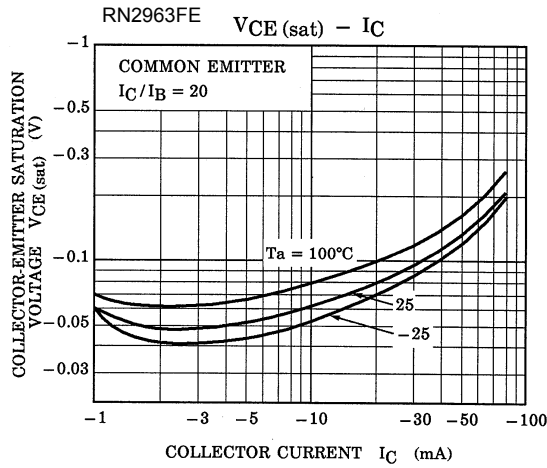
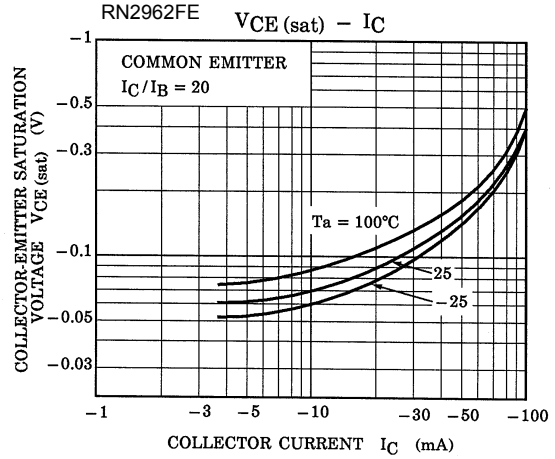
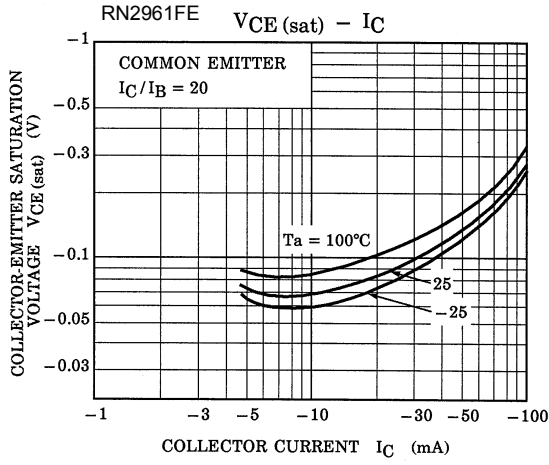
Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

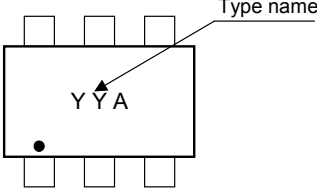
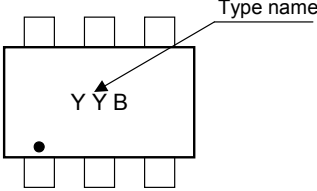
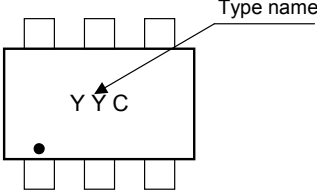
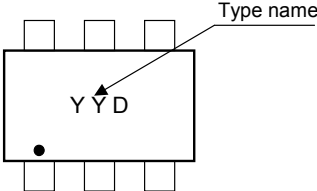
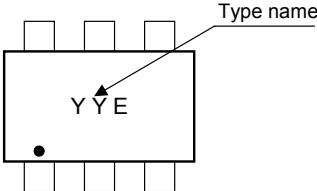
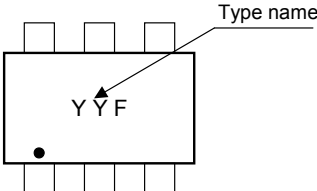
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2961FE~2966FE	I_{CBO}	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
		I_{CEO}	$V_{CE} = -50\text{ V}, I_B = 0$	—	—	-500	
Emitter cut-off current	RN2961FE	I_{EBO}	$V_{EB} = -10\text{ V}, I_C = 0$	-0.82	—	-1.52	mA
	RN2962FE			-0.38	—	-0.71	
	RN2963FE			-0.17	—	-0.33	
	RN2964FE			-0.082	—	-0.15	
	RN2965FE		$V_{EB} = -5\text{ V}, I_C = 0$	-0.078	—	-0.145	
	RN2966FE			-0.074	—	-0.138	
DC current gain	RN2961FE	h_{FE}	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	30	—	—	
	RN2962FE			50	—	—	
	RN2963FE			70	—	—	
	RN2964FE			80	—	—	
	RN2965FE			80	—	—	
	RN2966FE			80	—	—	
Collector-emitter saturation voltage	RN2961FE~2966FE	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	-0.1	-0.3	V
Input voltage (ON)	RN2961FE	$V_{I(ON)}$	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-1.1	—	-2.0	V
	RN2962FE			-1.2	—	-2.4	
	RN2963FE			-1.3	—	-3.0	
	RN2964FE			-1.5	—	-5.0	
	RN2965FE			-0.6	—	-1.1	
	RN2966FE			-0.7	—	-1.3	
Input voltage (OFF)	RN2961FE~2964FE	$V_{I(OFF)}$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-1.0	—	-1.5	V
	RN2965FE, 2966FE			-0.5	—	-0.8	
Transition frequency	RN2961FE~2966FE	f_T	$V_{CE} = -10\text{ V}, I_C = -5\text{ mA}$	—	200	—	MHz
Collector output capacitance	RN2961FE~2966FE	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF
Input resistor	RN2961FE	R1	—	3.29	4.7	6.11	kΩ
	RN2962FE			7	10	13	
	RN2963FE			15.4	22	28.6	
	RN2964FE			32.9	47	61.1	
	RN2965FE			1.54	2.2	2.86	
	RN2966FE			3.29	4.7	6.11	
Resistor ratio	RN2961FE~2964FE	R1/R2	—	0.9	1.0	1.1	
	RN2965FE			0.0421	0.0468	0.0515	
	RN2966FE			0.09	0.1	0.11	









Type Name	Marking
RN2961FE	
RN2962FE	
RN2963FE	
RN2964FE	
RN2965FE	
RN2966FE	

RESTRICTIONS ON PRODUCT USE

030619EAA

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.